Docket No.: MUH-12837

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : DIETMAR GOGL ET AL.

Filed : CONCURRENTLY HEREWITH

Title : METHOD FOR OPERATING AN MRAM SEMICONDUCTOR MEMORY CONFIGURATION

# INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

S i r :

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

U.S. Patent No. 5,703,805 (Tehrani et al.), dated December 30, 1997;

U.S. Patent No. 6,359,829 B1 (Van Den Berg), dated March 19, 2002 and corresponding European Patent Application EP 1 003 176 A2 (Van Den Berg), dated May 24, 2000;

Patent and Abstract of Japan 200187976 (Naoki), dated July 4, 2000;

Wang, Z. G. et al.: "Design, Simulation, and Realization of Solid State Memory Element Using the Weakly Coupled GMR Effect", IEEE Transactions on Magnetics, Vol. 32, No. 2, March 1996, pp. 520-526;

Zheng, Y. et al.: "Micromagnetic Principles in Pseudo Spin Valve Memory Element Design", IEEE Transactions on Magnetics, Vol. 33, No. 5, September 1997, pp. 3286-3288;

Wang, Z. et al.: "Quarternary Giant Magnetoresistance Random Access Memory", American Institute of Physics, J. Appl. Phys., Vol. 79, No. 8, April 15, 1996, pp. 6639-6641;

Wang, Z. G. et al.: "Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory", IEEE Transactions on Magnetics, Vol. 33, No. 6, November 1997, pp. 4498-4512;

International Search Report, dated January 10, 2003.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,

For Applicants WERNER H. STEMER
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Date: October 14, 2003

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| FORM PTO-1449 (SUBSTITUTE)<br><br>U.S. DEPARTMENT OF COMMERCE<br>PATENT AND TRADEMARK OFFICE<br><br>INFORMATION DISCLOSURE STATEMENT BY APPLICANT<br>(37 CFR 1.98(b)) | Attorney Docket No.: MUH-12837<br>Appl. No.:<br><br>Applicant: DIETMAR GOGL ET AL.<br><br>Filing Date: October 14, 2003<br>Group Art Unit: |
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| EXAMINER INITIALS | | PATENT NO. | DATE | PATENTEE | CLASS | SUB CLASS | FILING DATE |
|---|---|---|---|---|---|---|---|
| | A | 5,703,805 | 12/30/97 | Tehrani et al. | | | |
| | B | 6,359,829 B1 | 3/19/02 | Van Den Berg | | | |
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FOREIGN PATENT DOCUMENT

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| | J | 1 003 176 A2 | 5/24/00 | Europe | | | | |
| | K | 2000187976 | 7/4/00 | Japan | | | | |
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

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| | | Wang, Z. G. et al.: "Design, Simulation, and Realization of Solid State Memory Element Using the Weakly Coupled GMR Effect", IEEE Transactions on Magnetics, Vol. 32, No. 2, March 1996, pp. 520-526 |
| | | Zheng, Y. et al.: "Micromagnetic Principles in Pseudo Spin Valve Memory Element Design", IEEE Transactions on Magnetics, Vol. 33, No. 5, September 1997, pp. 3286-3288 |

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| | | Wang, Z. et al.: "Quarternary Giant Magnetoresistance Random Access Memory", American Institute of Physics, J. Appl. Phys., Vol. 79, No. 8, April 15, 1996, pp. 6639-6641 |
| | | Wang, Z. G. et al.: "Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory", IEEE Transactions on Magnetics, Vol. 33, No. 6, November 1997, pp. 4498-4512 |

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